L Number	Hits	Search Text	DB	Time stamp
1	117	(memory or transistor or dram or sdram or rom or prom or mosfet or fet or eeprom or nmos or pmos or eprom) and (gate) near8 (tungsten adj silicide or wsi or w adj si) near8 (titanium adj silicide or tisi or ti adj si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:00
2	5	(memory or transistor or dram or sdram or rom or prom or mosfet or fet or eeprom or nmos or pmos or eprom) and (gate) near10 (tungsten adj silicide or wsi or w adj si) near4 barrier same (titanium adj silicide or tisi or ti adj si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:03
3	27	(memory or transistor or dram or sdram or rom or prom or mosfet or fet or eeprom or nmos or pmos or eprom) and (gate) near5 barrier near5 (tungsten adj silicide or wsi or w adj si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:07
4	48	(mis or misfet) and (gate) with (tungsten adj silicide or wsi or w adj si) with (titanium adj silicide or tisi or ti adj si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:38
5	30	(static near2 memory or sram) same (dynamic near2 memory or dram) same sdram and (silicide) near4 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:43
6	20	silicide and extended near data near out near2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:44
7	74	silicide and (edodram or edoram or edorom or edo or edom)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 15:54
8	306	gate and source and drain and (edodram or edoram or edorom or edo or edom)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 16:10
9	165	gate and source and drain and (edodram or edoram or edorom or edo or edom) with (dram or sdram or rom or prom or eeprom or eprom or sram or ram)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 16:16
10	3	gate and source and drain and (edodram or edoram or edorom or edo or edom) with (dram or sdram or rom or prom or eeprom or eprom or sram or ram) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 16:16
-	10	(gate or word near line or wordline or transistor or fet or mosfet or sdram or rom or prom or dram) and (tungsten or titanium or w or ti or metal) near2 rich near2 (silicide or salicide) with (oxygen or oxide or oxidize or oxidized or oxidation or oxidization) with (nitride or nitrided or nitridation or nitradation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 14:34
-	22	(gate or word near line or wordline or transistor or fet or mosfet or sdram or rom or prom or dram) and (silicide or salicide or wsi or tisi) near3 (oxynitride or oxinitride or oxy-nitride) near5 (removal or removing or removed or remove or etch or etching or etched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 15:15
-	11	("4528066" | "4554050" | "5100826" | "5198384" | "5425392" | "5462638" | "5712168" | "5798296" | "5800726" | "5830798" | "5888894").PN.	USPAT	2004/06/29 14:40

-	17	("4528066" | "4554050" | "4900690" | "5023201" | "5100826" | "5198384" | "5202287" | "5425392" | "5462638" | "5712168" | "5798296" | "5800726" | "5801425" | "5830798" | "5888894" | "5960303" | "6136211").PN.	USPAT	2004/06/29 15:09
-	49	(gate or word near line or wordline or transistor or fet or mosfet or sdram or rom or prom or dram) and (titanium or tungsten or metal) near2 (oxynitride or oxinitride or oxy-nitride) near5 (removal or removing or removed or remove or etch or etching or etched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 15:24
-	36	(gate or word near line or wordline or transistor or fet or mosfet or sdram or rom or prom or dram) and ((titanium or tungsten or metal) near2 (oxynitride or oxinitride or oxy-nitride) or tion or won or ti near o near n or w near o near n or tio near n or wo near n) near5 (filament or protrusion or protuberance or projection or extrusion or protruding or extruding or projecting or short or shorting or shorted)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 15:32
-	75	((titanium or tungsten or metal) near2 (silicide or salicide) or tisi or wsi) same ((titanium or tungsten or ti or w) near (oxynitride or oxinitride or oxy-nitride or on or o near n)) and (etch or etching or etched or remove or removing or removal or removed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 15:34
-	27	((titanium or tungsten or metal) near2 (silicide or salicide) or tisi or wsi) same ((titanium or tungsten or ti or w) near (oxynitride or oxinitride or oxy-nitride or on or o near n)) same (etch or etching or etched or remove or removing or removal or removed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/29 15:42
-	44	(memory or transistor or dram or sdram or rom or prom or mosfet or fet) and (gate near electrode) near6 (tungsten adj silicide or wsi or w adj si) near6 (titanium adj silicide or tisi or ti adj si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/01 14:34